



SOT-23 Plastic-Encapsulate Transistors

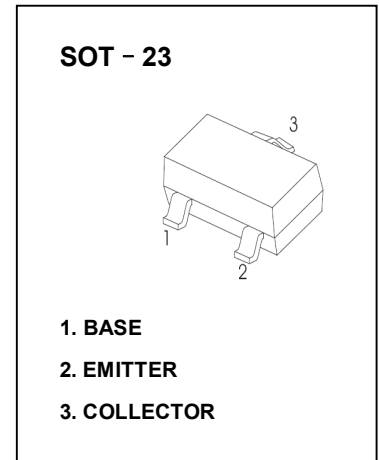
2SA1235A TRANSISTOR (PNP)

FEATURES

- Low Collector Current
- Low Collector Power Dissipation

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-60	V
V _{CE0}	Collector-Emitter Voltage	-50	V
V _{EB0}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-200	mA
P _C	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-0.1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-100	nA
DC current gain	h _{FE(1)}	V _{CE} =-6V, I _C =-1mA	150		500	
	h _{FE(2)}	V _{CE} =-6V, I _C =-0.1mA	90			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-6V, I _C =-10mA		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-6V, I _E =0, f=1MHz		4		pF

CLASSIFICATION OF h_{FE(1)}

RANK	M-E	M-F
RANGE	150-300	250-500
MARKING	M-E	M-F

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